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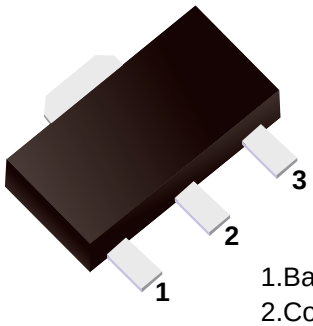
2SB1132

PNP Transistors



1.Base
2.Collector
3.Emitter

Simplified outline(SOT-89)

Features

- Low $V_{CE(sat)}$
- Compliments to 2SD1664

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-1	A
Single pulse, Pw=100ms		-2	A
Collector Power Dissipation	P_C *	0.5	W
Jumction temperature	T_j	150	℃
Storage temperature Range	T_{stg}	-55 to +150	℃

* When mounted on a 40x40x0.7mm ceramic board.

Electrical Characteristics Ta = 25℃

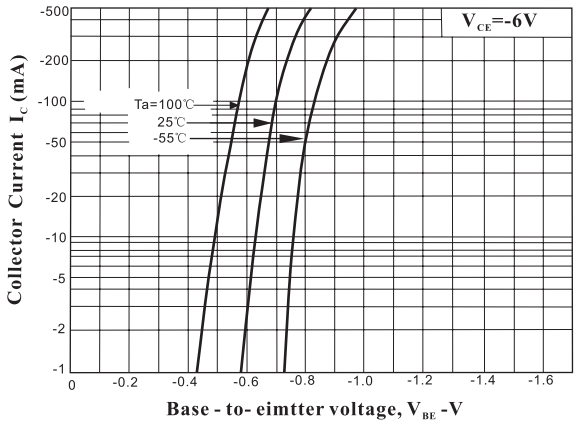
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -50μA, I_E=0	-40			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-32			
Emitter - base breakdown voltage	V_{EBO}	I_E= -50μA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -20 V , I_E=0			-0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-50mA		-0.2	-0.5	V
DC current gain	h_{FE}	V_{CE}= -3V, I_C= -0.1A	82		390	
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0mA,f=1MHz		20	30	pF
Transition frequency	f_T	V_{CE}= -5V, I_E= 50mA,f=30MHz		150		MHz

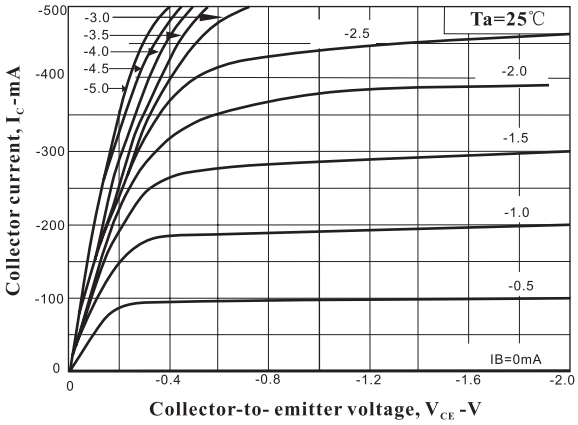
h_{FE} Classification

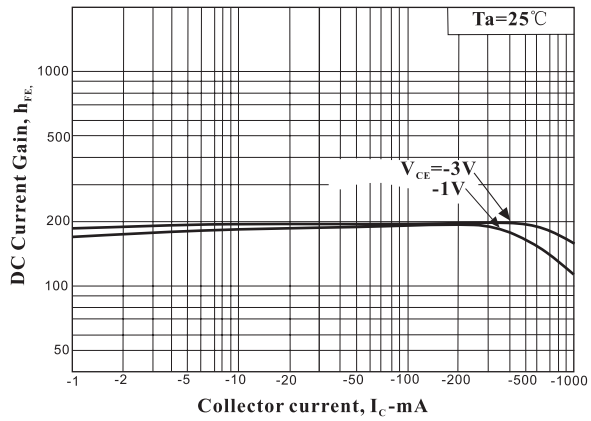
Type	2SB1132-P	2SB1132-Q	2SB1132-R
Range	82-180	120-270	180-390
Marking	BAP*	BAQ*	BAR*

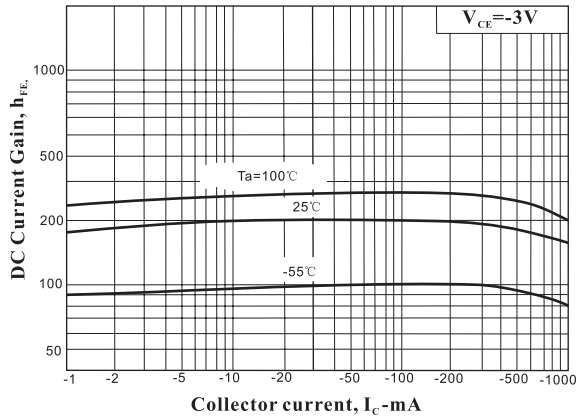
2SB1132

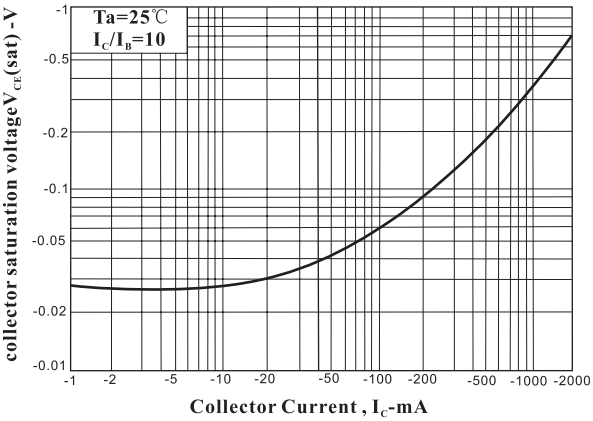
■ Typical Characterisitics

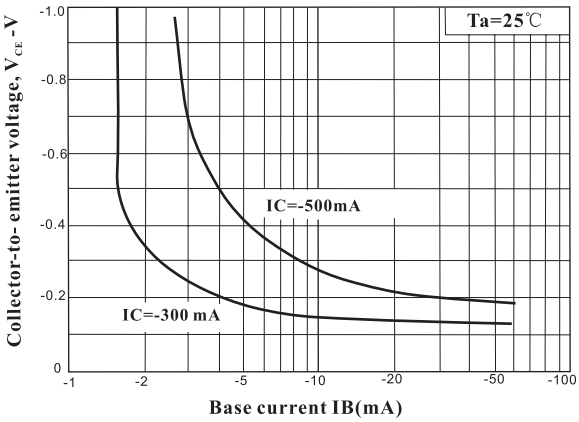












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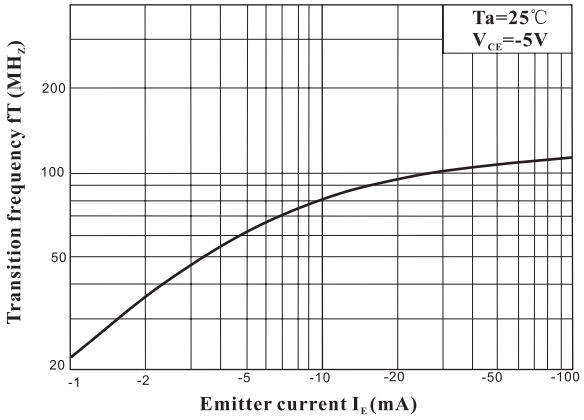

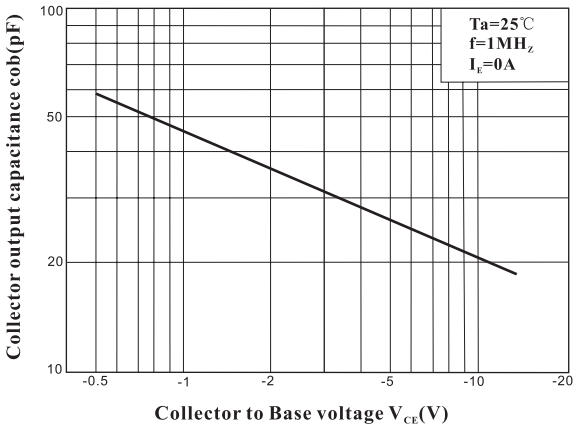

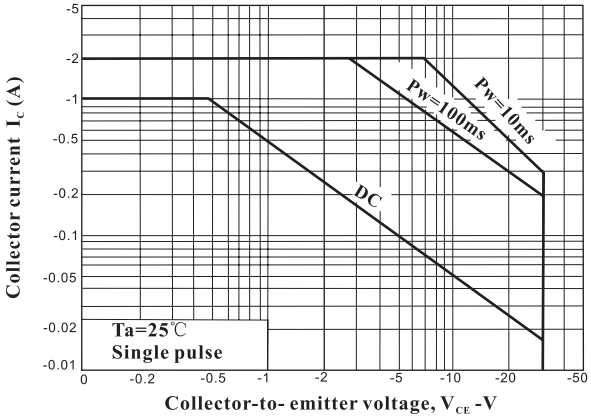

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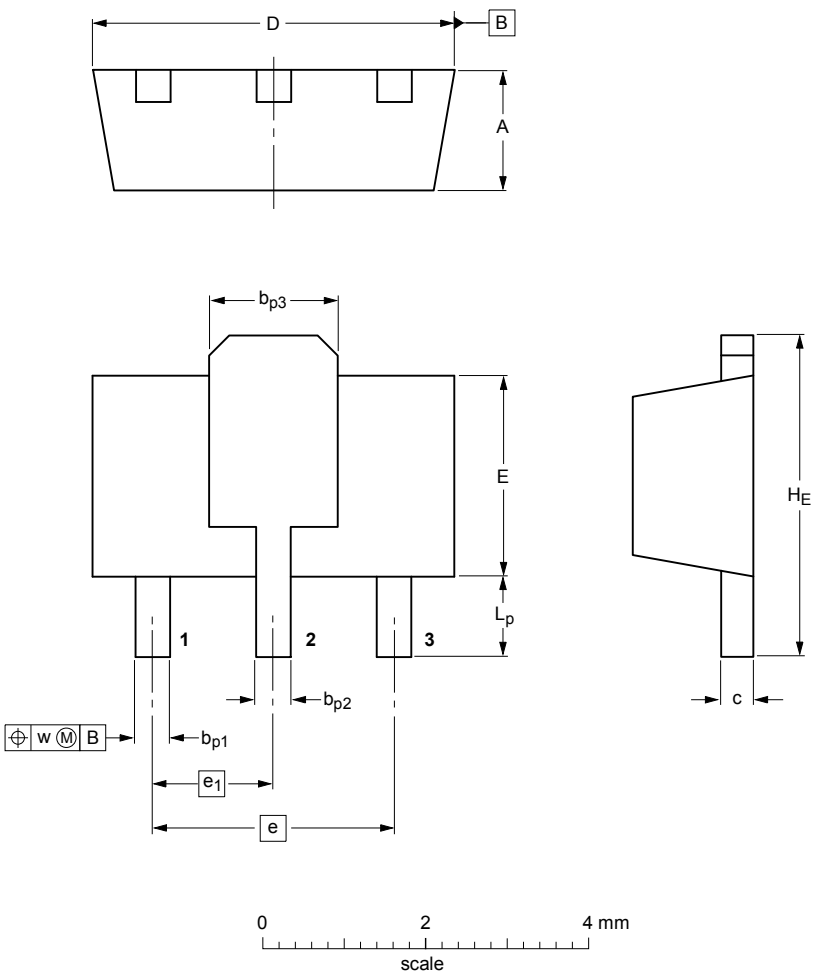
■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13